

Fragility of Pb modified germanium chalcogenide glasses

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Abstract Bulk chalcogenide glasses with compositions $Pb_x Ge_{42,x} Se_{58} (3 \le x \le 15)$ (series I), $Pb_{v_0} Ge_x Se_{80,x} (17 \le x \le 24)$ (series II), $Pb_x Ge_{42,x} Se_{48} Te_{v_0} (3 \le x \le 15)$ (series III) and $Pb_{20} Ge_x Se_{70,x} Te_{v_0} (17 \le x \le 24)$ (series IV) were prepared by the melt quenching technique. The heat capacity jump at glass transition (ΔC_p) and the activation energy for viscous flow (E_η) of the four series of glasses were obtained from differential scanning calorimetry (DSC) studies. The composition dependence of ΔC_p and E_η of series I and III showed minima near the composition with x = 9 at wt % Pb Similarly the ΔC_p and E_η could be associated with the fragility of the glass network the data obtained have been used to understand the changes occurring in the glass network as a function of composition. The results have also been discussed in the light of the majority charge carrier reversal occurring at the specific compositions in the respective series of glasses.

Keywords Chalcogenide glasses, fragility, heat capacity jump, activation energy

PACS Nos. 61 43Fs, 64 70Pf, 65 60+a

1. Introduction

Chalcogenide glasses are generally *p*-type semiconductors with the Fermi level pinned near the middle of the band gap by charged defects present in these glasses [1] After the pioneering work by Toghe *et al* [2], it is now generally accepted that incorporation of appropriate amounts of either Bismuth (Bi) [2] or Lead (Pb) [3] in bulk Ge-Se glasses leads to the reversal of the majority charge carrier from *p*- to *n*-type. Attempts have been made to attribute the majority charge carrier reversal (MCCR) phenomenon in Bi modified Ge-Se glasses to percolation of Bi clusters [4], high degree of polarisation of Bi [5], existence of defect states [6], *etc.* The MCCR in Pb modified Ge-Se glasses has been attributed [7] to changes induced in electronic structure of the glass by the energetically disposed sp³d² band of Pb. Electrical properties of Pb_xGe_{42-x}Se₄₈Te₁₀ glasses indicate

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[11] that MCCR occurs in this glass system at $x \approx 9$ at. wt. of Pb. It is worthy to point out that calorimetric parameters of Bi and Pb modified chalcogenide glasses [8-12], such as glass transition temperature (T_g) and crystallisation temperature (T_c), heat capacity jump at glass transition, activation energies and thermal diffusivity [13, 14] consistently show anomalous features at the compositions at which the conduction type change occurs Glass forming liquids are classified as 'fragile' or 'strong' on the basis of the magnitude of the heat capacity jump at T_g as well as from the extent of deviation of viscosity versus temperature Arrehenius plots [15]. However, the effect of compositional variation on glassy network has not been investigated in detail in Pb-Ge-Se(-Te) glasses. Differential scanning calorimetic (DSC) study of two series of Pb-Ge-Se and Pb-Ge-Se-Te glasses has been taken up to understand the changes occurring in the glassy network as a function of composition by evaluating the different factors contributing to the fragility of glass.

2. Experimental

The melt quenching technique was used to prepare bulk glasses with composition $Pb_xGe_{42-x}Se_{58}$ (0 $\le x \le 15$) (series I), $Pb_{20}Ge_xSe_{80-x}$ (17 $\le x \le 24$) (series II), $Pb_xGe_{42-x}Se_{48}Te_{10}$ (0 $\le x \le 15$) (series III) and $Pb_{20}Ge_xSe_{70-x}Te_{10}$ (17 $\le x \le 24$) (series IV) Appropriate amounts of high purity (99.999%) elements sealed in fused silica ampoules under a vacuum of 10⁻⁵ mbar were slowly heated to 1300 K in a rotary furnace. After providing sufficient time for homogenisation at this temperature, the ampoules were suddenly dropped into cold water to form glass. The amorphous nature of as-guenched glass samples was verified by X-ray diffraction technique. The majority charge carrier type in each composition was determined from the sign of the Seebeck coefficient. Thermoelectric power measurements performed on thin slices of as guenched glasses established that the MCCR occurred at Pb concentration of ~9 at. wt. % in the series I and III, and at Ge concentration of ~21 at, wt. % in the series II and IV. Non-isothermal studies were performed with a Perkin-Elmer DSC 7 differential scanning calorimeter. Constant heating rates ranging from 5 °C.min⁻¹ to 25 °C.min⁻¹ were used. All the DSC runs were performed using alumina sample pans under dry nitrogen atmosphere. The instrument was calibrated with indium and zinc melting point standards prior to data collection. Standard software supplied along with the DSC instrument was used for obtaining the characteristic temperatures and heat capacity data from the DSC curves.

3. Results and discussion

The kinetic parameters of glass transition and crystallisation can be estimated from the DSC data by several methods [16,17], which are based on the assumption that the temperature of a kinetically controlled reaction shifts with heating rate. According to one such method due to Bartenev [18],

$$d[\ln(\phi)]/d[1/T_g] = -E_{\eta}/R \tag{1}$$

where ϕ is the heating rate, E_{η} is the activation energy of the kinetic reaction, T_g is the glass transition temperature and R is the universal gas constant. The activation energy

 E_{η} is also referred to [19] as the activation energy for viscous flow. The degree of fragility <m> [20] of the glass at the glass transition is given by,

$$\langle m \rangle = E_{\eta} / (2.3R T_g) \tag{2}$$

The activation energy of viscous flow (E_{η}) estimated from the slope of the ln(ϕ) versus 1000/ T_g plots for two series of Pb-Ge-Se and Pb-Ge-Se-Te glasses are shown in Figure 1 and Figure 2, respectively T_g values obtained at heating rates of 5, 10, 15, 20 and 25°C min¹ from DSC measurements plotted and fitted using least squares fitting procedure for determining E_{η} . Since the kinetically controlled reaction is the glass transition and the estimated activation energy is a measure of the hindrance or resistance posed by the glassy network to the glass transition phenomenon, it can be concluded from the figures that the glass transition is least hindered for the glasses at x = 9 at wt % Pb in series I and III, and at x = 21 at wt % Ge in series II and IV A minimum in the activation energy also implies that the glasses at these compositions undergo minimal configurational changes at the glass transition. The activation energy values obtained for the two series of glasses are tabulated in Table 1.

| Glass Composition | <i>E</i> _η (kJ mole ¹) | т _, (К) | <m></m> | <i>∆C_p</i> (Jg ¹K ¹) | Glass Composition | E _n (kJmole ¹) | т _а (К) | <m></m> | <i>∆C_p</i> (Jg ¹ K ¹) |
|---|--|-----------------------|---------|------------------------------------|---|--|-----------------------|---------|--|
| Series I | | | | | Series II | | | | |
| Pb ₀₃ Ge ₃₆ Se ₅₈ | 392 | 544 | 37 7 | 0 44 | Pb ₂₀ Ge ₁₇ Se ₆₃ | 298 | 49 5 | 31 5 | 0 45 |
| Pb₀cGe ₃₆ Se ₅₈ | 335 | 527 | 33 3 | 0 19 | Pb ₂₀ Ge ₁₉ Se ₆₁ | 251 | 533 | 24 6 | 0 17 |
| Pb ₍₉₉ Ge ₃₃ Se ₅₈ | 272 | 524 | 27 2 | 0 16 | Pb ₂₀ Ge ₂₁ Se ₅₉ | 205 | 544 | 19 7 | 0 15 |
| Pb, Ge ₂₉ Se ₅₈ | 294 | 527 | 29 2 | 0 20 | Pb ₂₀ Ge _{22 5} Se _{57 5} | 334 | 535 | 32 7 | 0 19 |
| Pb ₁ Ge ₂₇ Se ₅₈ | 380 | 530 | 37 5 | 0 28 | Pb ₂₀ Ge ₂₄ Se ₅₆ | 360 | 524 | 35 9 | 0 45 |
| Series III | | | | | Series IV | | | | |
| Pb ₀₃ Ge ₃₉ Se ₄₈ Te ₁₀ | 407 | 536 | 39 7 | 0 34 | Pb ₂₀ Ge ₁₇ Se ₅₃ Te ₁₀ | 298 | 496 | 31 4 | 0 20 |
| Рb ₀₆ Ge ₃₆ Se ₄₈ Te ₁₀ | 268 | 522 | 26 9 | 0 26 | Pb ₂₀ Ge ₁₉ Se ₅₁ Te ₁₀ | 213 | 510 | 21 9 | 0 18 |
| Pb ₀₉ Ge ₃₃ Se ₄₈ Te ₁₀ | 249 | 517 | 25 2 | 0 21 | Pb ₂₀ Ge ₂₁ Se ₄₉ Te ₁₀ | 208 | 518 | 21 0 | 0 13 |
| Pb ₁₃ Ge ₂₉ Se ₄₈ Te ₁₀ | 245 | 514 | 24 9 | 0 25 | Pb ₂₀ Ge _{22 5} Se _{47 5} Te ₁₀ | 303 | 516 | 30 7 | 0 18 |
| Pb ₁₅ Ge ₂₇ Se ₄₈ Te ₁₀ | 313 | 515 | 31 8 | 0 28 | Pb ₂₀ Ge ₂₄ Se ₄₆ Te ₁₀ | 329 | 508 | 33 9 | 0 20 |

Table 1 Activation energy of viscous flow (E_η) glass transition temperature @ 20 °C min⁻¹ degree of fragility <*m*> and heat capacity jump at T_q (C_p) of various compositions of Pb-Ge-Se(-Te) glasses

The degree of fragility values estimated for various glass compositions in the four series of glasses are listed in Table 1. The E_{η} and T_g values used for estimating $\langle m \rangle$ are also listed in Table 1. $\langle m \rangle$ varied between 197 ± 0.4 and 397 ± 0.4. These low $\langle m \rangle$ values are signatures of the 'strong' nature of covalently bonded chalcogenide glasses.

However, a consistent variation in <m> value could be seen within each series with a minimum near at x = 9 at. wt. % Pb in series I and III, and at x = 21 at. wt. % Ge in series II and IV. Hence, one can conclude that <m> values also indicate a minimum in fragility at the compositions at which the *p*- to *n*-type carrier change occurs in Pb-Ge-Se [3,21] and Pb-Ge-Se-Te [11,21] glasses. When <m> is minimum, the glass and its high temperature crystalline phase have minimum configurational difference. This factor is combination with the directional nature of the covalent bond existing between the elements seems to provide a favourable situation for the electronic interaction leading to the unpinning of the Fermi energy level towards the conduction band [21].



Figure 1. Variation of activation energy of viscous flow (E_{η}) as a function of composition of $Pb_xGe_{42-x}Se_{58}$ ($3 \le x \le 15$) (series I) and $Pb_{20}Ge_xSe_{80-x}$ ($17 \le x \le 24$) (series II) glasses Dotted line merely connects adjacent data points

The heat capacity (specific heat at constant pressure) jump at the glass transition temperature is an inherent property of a glass [22]. The heat capacity jump (also referred to as the excess heat capacity at T_o), is expressed as $\Delta C_p = (C_{pl} - C_{pg})_{T-T_o}$, where C_a



Figure 2. Variation of activation energy of viscous flow (E_{η}) as a function of composition of Pb_xGe_{42-x}Se₄₈Te₁₀ ($3 \le x \le 15$) (series III) and Pb₂₀Ge_xSe_{70-x}Te₁₀ ($17 \le x \le 24$) (series IV) glasses. Dotted line merely connects adjacent data points.

and C_{pg} are the heat capacity of the liquid and the glassy states across the glass transition. The value of the excess heat capacity reflects the amount of configuration change occurring in the network at the glass to liquid transition. According to Angell [23], ΔC_p could be correlated [24] with the fragility of a glass. Fragile glasses exhibiting a large ΔC_p undergo more configurational change at the glass transition. Strong glasses exhibit a small ΔC_p and minimal configuration changes at T_g . The variation of the heat capacity jump at T_g (ΔC_p) of the four series of glasses is shown in Figure 3 and Figure 4, respectively. The



Figure 3. Variation of heat capacity jump at T_q (ΔC_p) as a function of composition of $Pb_x Ge_{42,x} Se_{58}$ (3 $\cdot \lambda \cdot 15$) (series I) and $Pb_{20} Ge_x Se_{80,x}$ (17 $\leq x \leq 24$) (series II) glasses Dotted line merely connects adjacent data points

excess heat capacity at the T_g shows a minimum near the composition with x = 9 at. wt. % Pb for series I and III, and x = 21 at. wt. % Ge for series II and IV, which are the compositions at which the *p*- to *n*-type transition occurs [3,11,21]. Thus the minimum in fragility is associated with the composition at which MCCR occurs in these glasses. A small ΔC_p is also a proof of a strong thermodynamic behaviour which indicates that the



Figure 4. Variation of heat capacity jump at $T_g(\Delta C_p)$ as a function of composition of $Pb_xGe_{42\cdot x}Se_{48}Te_{10}$ (3 $x \le 15$) (series III) and $Pb_{20}Ge_xSe_{70\cdot x}Te_{10}$ (17 $\le x \le 24$) (series IV) glasses. Dotted line merely connects adjacent data points.

glass is not far away from its thermodynamic equilibrium. A minimum in ΔC_p has been observed when glasses undergo a floppy to rigid transition [25,26] in Ge-As-Se [27] Ge-Sb-Se [28,29], Ge-As-Te and Si-As-Te [29] glasses. In the case of Pb-Ge-Se-Te glasses the composition dependence of T_g suggests the presence of a relatively large number of hetero-nuclear bonds near the compositions at which the p- to n-type transition occurs. This could give rise to an optimally coordinated 3-d structure, leading a rigid glassy network as reflected by the minimum in the excess heat capacity data.

4. Conclusions

The composition dependence of E_{η} , <m> and ΔC_{p} of two series of Pb-Ge-Se and Pb Ge-Se-Te glasses has been obtained from DSC data. These parameters show subtle variation in their values among the different series of glasses. These variations are to be expected since the percentages of group IV and VI elements vary in each of these series of glasses, leading to variation in the nature of the bonding between the atoms. But within each series, the composition dependence of E_{η} , <m> and ΔC_{p} consistently show a minimum at x = 9 at. wt. % Pb and x = 21 at wt. % Ge, for both the Pb-Ge-Se and Pb Ge-Se-Te glasses, which are the compositions at which the conduction type change occurs This clearly shows evidence of a fragility change associated with the conduction mechanism change. Although the change in conduction mechanism is an electronic property, the current results clearly indicate that there is a structural basis to the electronic transition occurring at specific compositions in the lead modified chalcogenide glasses.

Acknowledgment

Financial assistance from the Department of Atomic Energy, Government of India is gratefully acknowledged.

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